

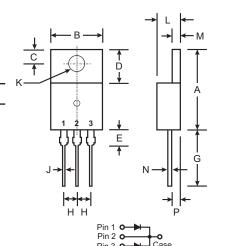
### 30A DUAL LOW VF SCHOTTKY BARRIER RECTIFIER

### **Features**

- Low Power Loss, High Efficiency
- Guard Ring for Transient Protection
- High Surge Capability
- Very Low Forward Voltage Drop
- For Use in High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Lead Free Finish, RoHS Compliant (Note 1)

### **Mechanical Data**

- Case: TO-220AB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Tin Finish. Solderable per MIL-STD-202, Method 208 (§3)
- Polarity: See Diagram
- Marking: Type Number
- Ordering Information: See Sheet 3
- Weight: 2.24 grams (approximate)



TO-220AB			
Dim	Min	Max	
Α	14.22	15.88	
В	9.65	10.67	
С	2.54	3.43	
D	5.84 6.86		
E		6.35	
G	12.70	14.73	
Н	2.29	2.79	
J	0.51	1.14	
K	3.53∅	4.09∅	
L	3.56	4.83	
M	1.14	1.40	
N	0.30	0.64	
Р	2.03	2.92	
All Dimensions in mm			

## **Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Characteristic		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	30	V
RMS Reverse Voltage		V <sub>R(RMS)</sub>	21	V
Average Rectified Output Current @ T <sub>C</sub> = 140°C	Total Device Per Element	Io	30 15	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load Per Element		I <sub>FSM</sub>	260	Α
Peak Repetitive Reverse Current Per Element at t <sub>P</sub> = 2μs, 1 KHz		I <sub>RRM</sub>	1.0	А
Voltage Rate of Change		dV/dt	10,000	V/μs
Typical Thermal Resistance Junction to Case (Note 2)	Per Diode Total	R <sub>eJC</sub>	1.5 0.8	°C/W
Operating Temperature Range		Tj	-65 to +150	°C
Storage Temperature Range		T <sub>STG</sub>	-65 to +150	°C

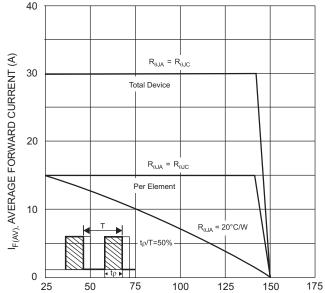
## **Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 3)	V <sub>(BR)R</sub>	30	_	_	V	I <sub>R</sub> = 1.5mA
Forward Voltage Per Element	V <sub>F</sub>		 0.52 	0.46 0.38 0.57 0.50	V	
Peak Reverse Current Per Element (Note 3)	I <sub>R</sub>			1.0 300	mA mA	$@V_R = 30V, T_j = 25^{\circ}C \\ @V_R = 30V, T_j = 125^{\circ}C \\$

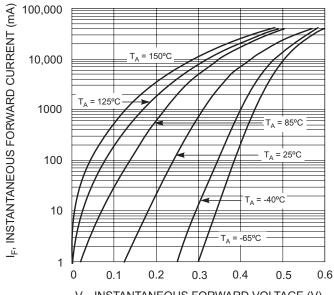
Notes: 1. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex, Notes 5 and 7.

- 2. Thermal Resistance Junction to Case: Device mounted on 200x200x5mm aluminum plate.
- 3. Short duration test pulse used to minimize self-heating effect.

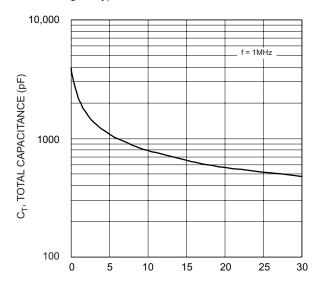




T<sub>C</sub>, CASE TEMPERATURE (°C) Fig. 1 Forward Current Derating Curve



V<sub>F</sub>, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 3 Typical Forward Characteristics, Per Element



 $\label{eq:VR} {\rm V_R,\,REVERSE\,\,VOLTAGE\,\,(V)}$  Fig. 5 Typical Total Capacitance, Per Element

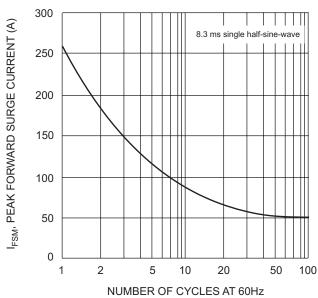
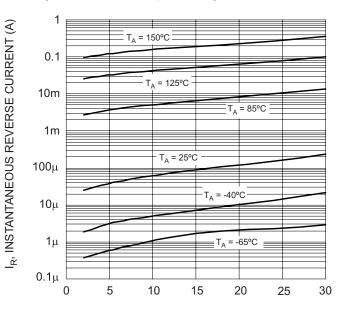


Fig. 2 Maximum Non-Repetitive Surge Current, Per Element



 $V_R$ , INSTANTANEOUS REVERSE VOLTAGE (V) Fig. 4 Typical Reverse Characteristics, Per Element



# Ordering Information (Note 4)

Device	Packaging	Shipping
SBL30L30CT	TO-220AB	50/Tube

Notes:

4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

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